



**MMBT2222A**  
**NPN TRANSISTOR**

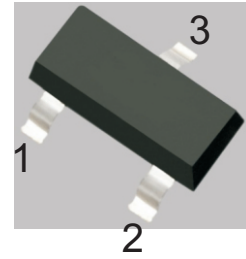
**FEATURES**

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A)

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current — Continuous	$I_C$	600	mA
Collector Power Dissipation	$P_C$	300	mW
Thermal Resistance From Junction To Ambient	$R_{thJA}$	417	°C/W
Operation Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

**SOT-23**



1.BASE  
2.EMITTER  
3.COLLECTOR

**CLASSIFICATION OF  $h_{FE}$**

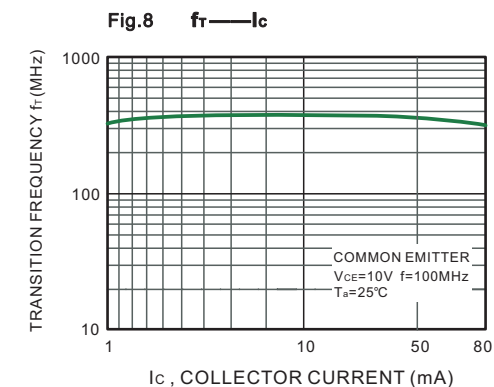
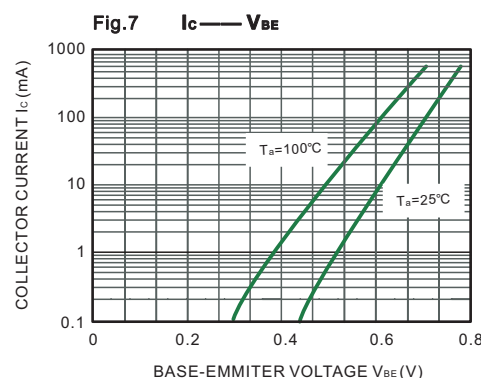
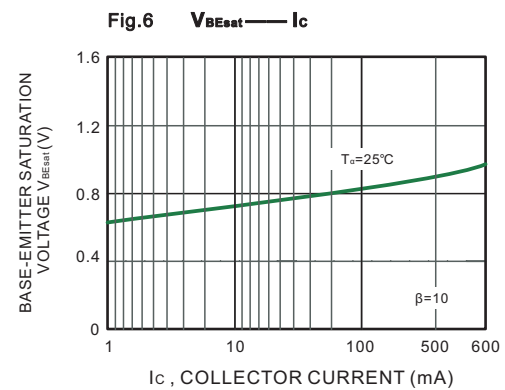
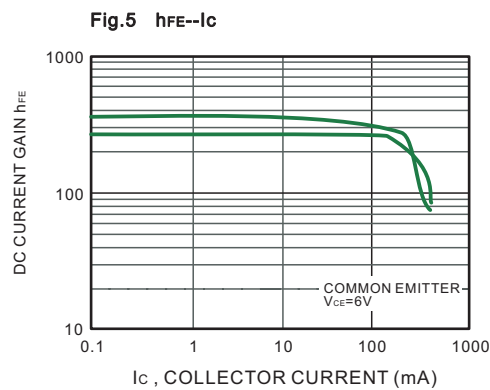
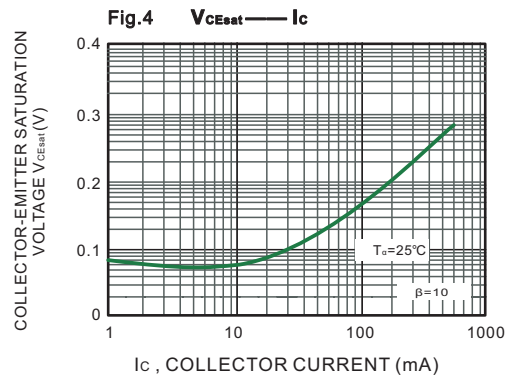
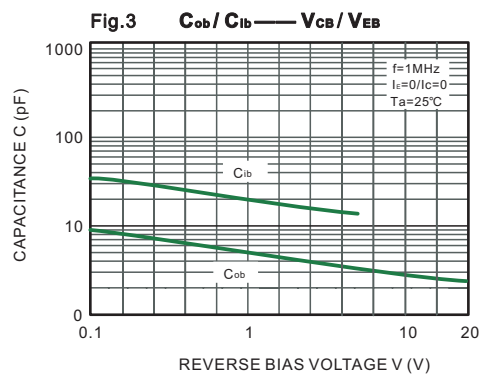
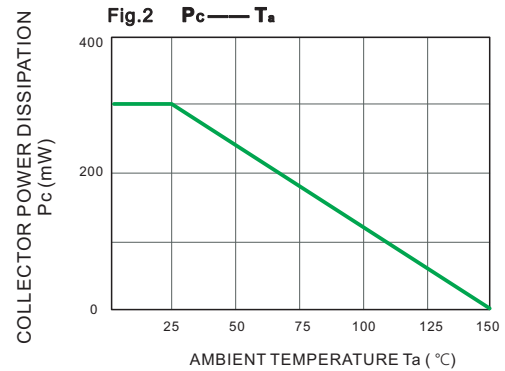
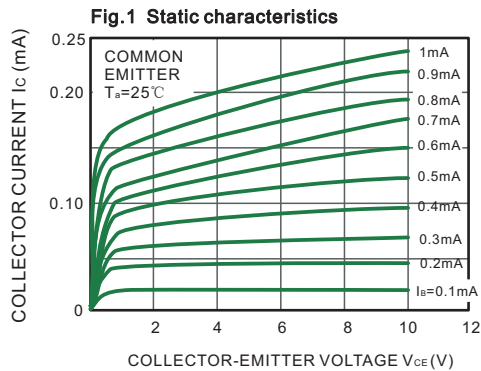
Rank	L	H
Range	100-200	200-300
Marking	1P	

**ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 60V, I_E = 0$			0.01	$\mu A$
Collector cut-off current	$I_{CEX}$	$V_{CE} = 30V, V_{BE(off)} = 3V$			0.01	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 3V, I_C = 0$			0.1	$\mu A$
DC current gain	$h_{FE1}$	$V_{CE} = 10V, I_C = 150\text{mA}$	100		300	
	$h_{FE2}$	$V_{CE} = 10V, I_C = 0.1\text{mA}$	40			
	$h_{FE3}$	$V_{CE} = 10V, I_C = 500\text{mA}$	42			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.0 0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$			2.0 1.2	V
Transition frequency	$f_T$	$V_{CE} = 20V, I_C = 20\text{mA}, f = 100\text{MHz}$	300			MHz
Delay time	$t_d$	$V_{CC} = 30V, V_{BE(off)} = -0.5V, I_C = 150\text{mA}, I_{B1} = 15\text{mA}$			10	ns
Rise time	$t_r$				25	ns
Storage time	$t_s$	$V_{CC} = 30V, I_C = 150\text{mA}, I_{B1} = -I_{B2} = 15\text{mA}$			225	ns
Fall time	$t_f$				60	ns

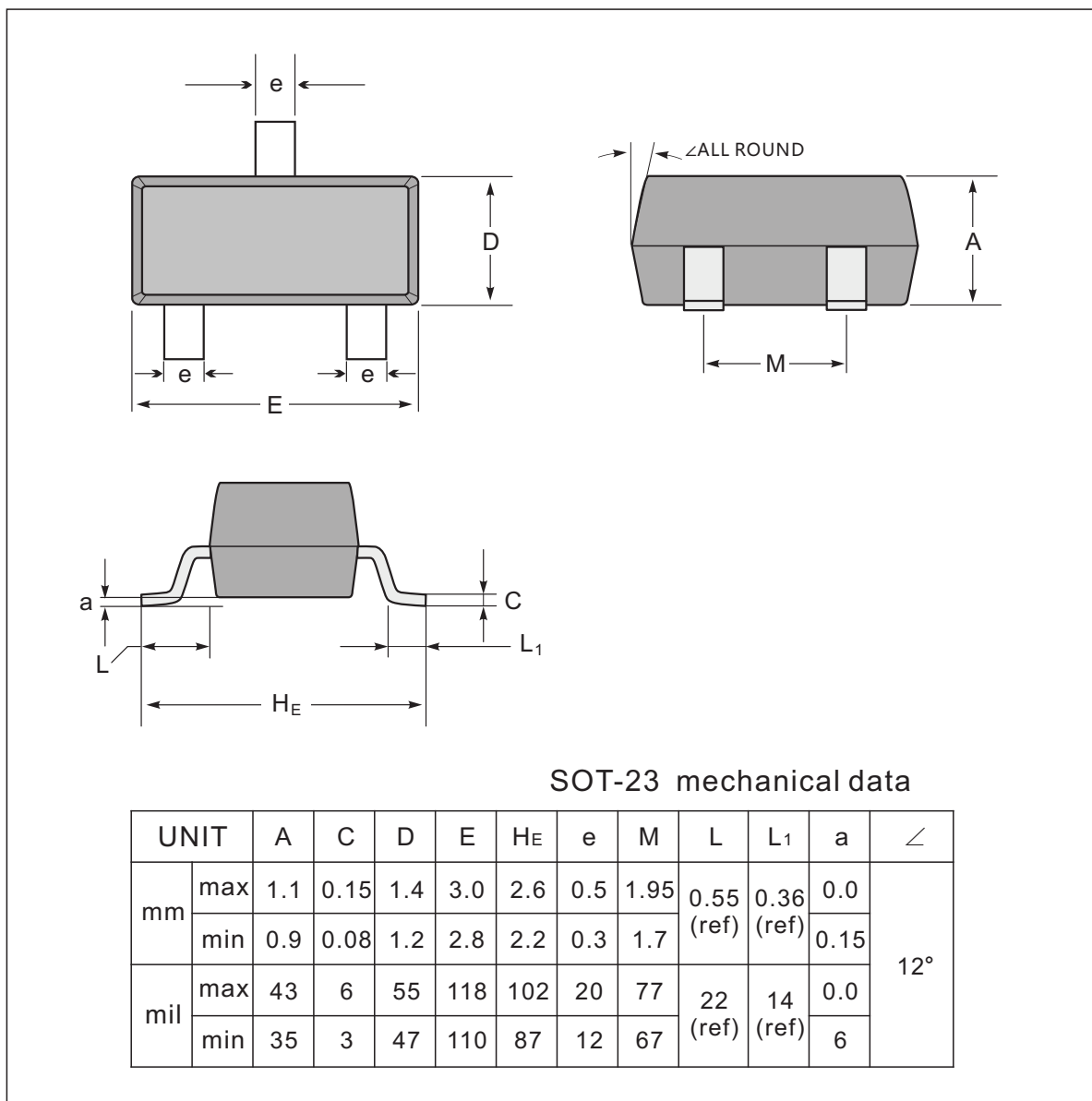


### TYPICAL CHARACTERISTICS

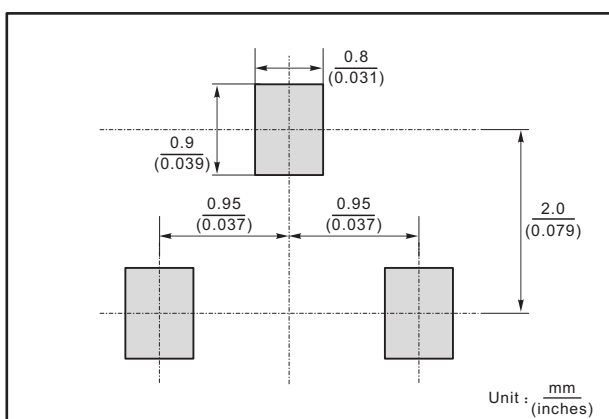




### SOT-23 Package Outline Dimensions



#### The recommended mounting pad size



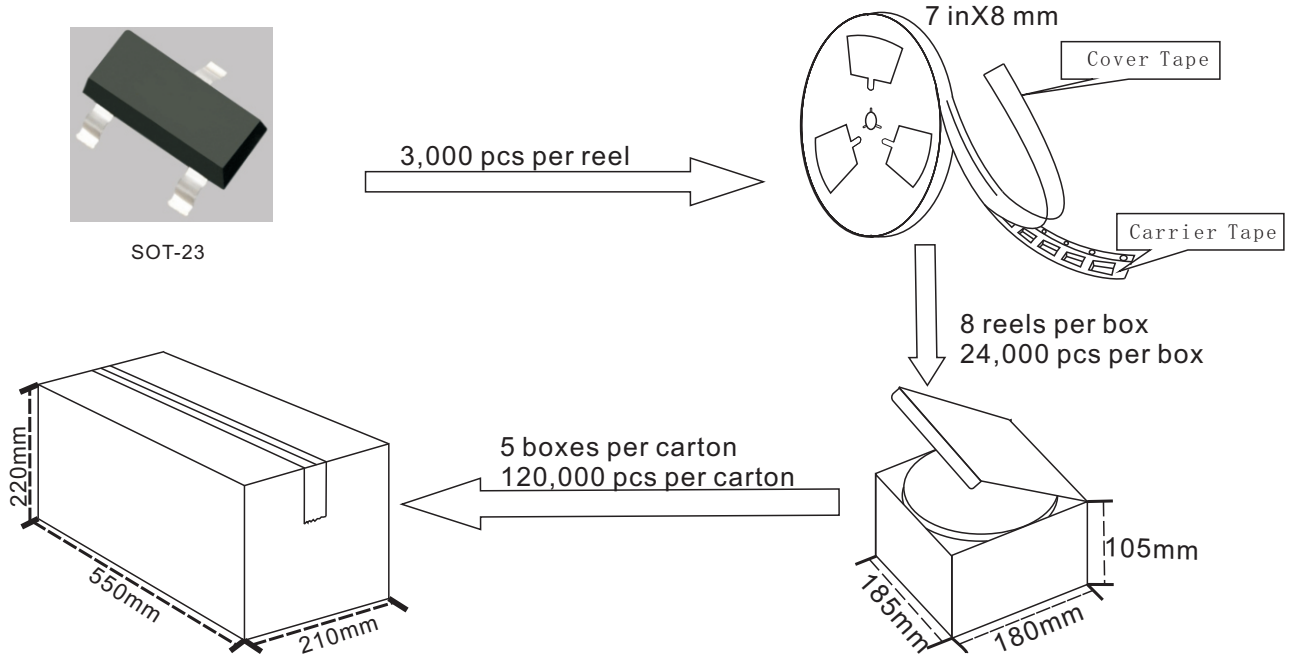
#### Marking

Type number	Marking code
MMBT2222A	1P

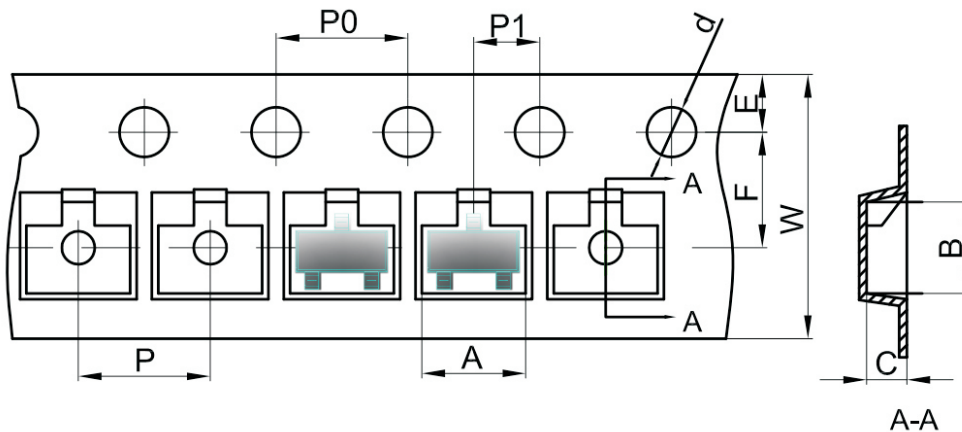


## SOT-23 Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



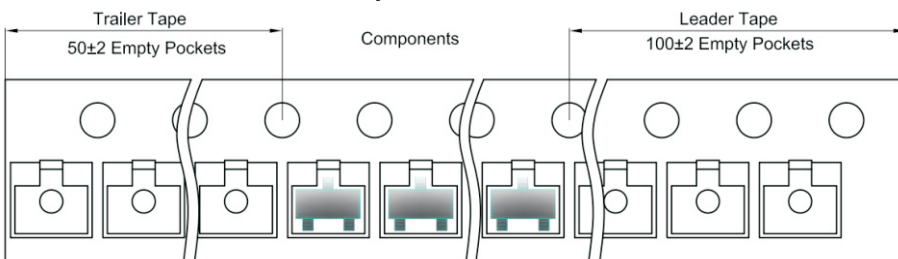
### SOT-23 Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

### SOT-23 Tape Leader and Trailer



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